

## **Product / Process Change Notice**

### **Parts Affected:**

Chip process CP207, NPN silicon high speed saturated switching transistors, wafers, and bare die.

### **Extent of Change:**

The CP207 wafer process has been discontinued and replaced with the CP396V wafer process.

The overall wafer diameter is being increased from 4 inch to 5 inch.

The overall wafer thickness is being reduced from 8.0 mils to 7.1 mils.

The die size and die pattern have been changed; see figures 1 and 2 for details.

### **Reason for Change:**

An alternate wafer foundry was approved for this process.

### **Effect of Change:**

This change does not affect the electrical characteristics of any device.

### **Qualification:**

Standard evaluation and qualifications completed resulting in no performance differences compared to current product.

### **Effective Date of Change:**

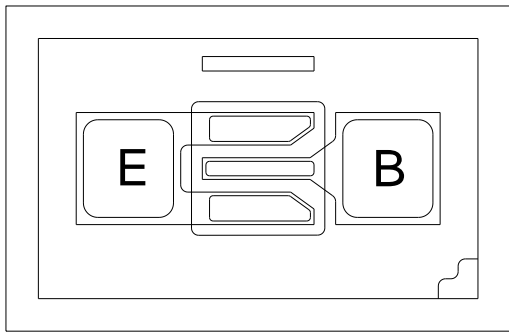
Existing inventory will be shipped until depleted.

### **Sample Availability:**

Please contact Salesperson or Manufacturer's Representative.

**Figures:**

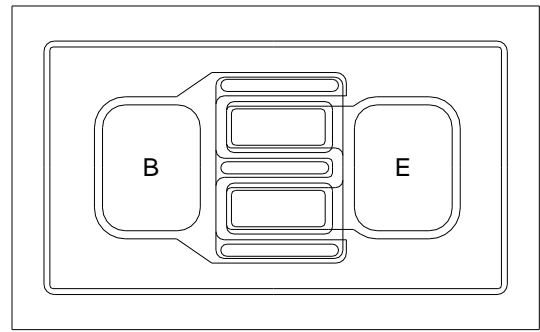
**Figure 1: CP207 Chip Geometry (Discontinued)**



BACKSIDE COLLECTOR

Wafer Diameter: 4 inch  
Die Size: 9.0 x 14 mils  
Die Thickness: 8.0 mils  
Bond Pad Size (Emitter): 2.7 x 2.7 mils  
Bond Pad Size (Base): 2.7 x 2.7 mils  
Topside Metal: Al (13,000Å)  
Backside Metal: Au (6,000Å)

**Figure 2: CP396V Chip Geometry**



BACKSIDE COLLECTOR

Wafer Diameter: 5 inch  
Die Size: 14.2 x 8.7 mils  
Die Thickness: 7.1 mils  
Bond Pad Size (Emitter): 2.9 x 3.7 mils  
Bond Pad Size (Base): 2.9 x 3.7 mils  
Topside Metal: Al (13,000Å)  
Backside Metal: Au-As (9,000Å)

**Part Numbers Affected:**

2N2205	2N784A
2N2242	2N834A
2N2369A	2N835
2N2369A	2N914
2N2475	2N947
2N3011	BSX20
2N3210	BSY18
2N3508	BSY62
2N706A	BSY95A
2N706C	CMPT2369
2N708	CP207-2N2369A-CT
2N709	CP207-2N2369A-WN
2N709A	MD2369B
2N744A	MPQ2369
2N753	PN2369A